

General Description

The 3N120 uses advanced planar stripe DMOS technology and design to provide excellent RDS(ON).

These devices are well suited for high efficiency switch mode power supply.

Features

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS Compliant

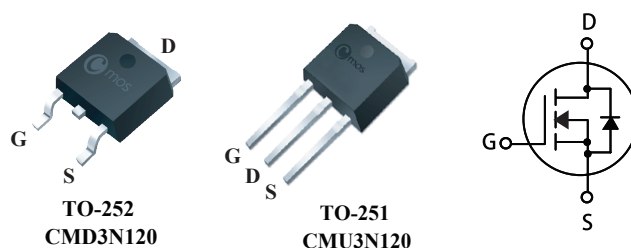
Product Summary

BVDSS	RDSON	ID
1200V	6.4Ω	3A

Applications

- DC-DC Converters
- Power switching application

TO-252/251 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	1200	V
V_{GS}	Gate-Source Voltage	±30	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	3	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	1.8	A
I_{DM}	Pulsed Drain Current	12	A
EAS	Single Pulse Avalanche Energy ¹	62.5	mJ
P_D	Total Power Dissipation	100	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	100	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	1.25	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	1200	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=1.5A$	---	5.7	6.4	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	3	---	5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=1200V$, $V_{GS}=0V$	---	---	25	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=30V$, $I_D=1.5A$	---	4	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	3.3	---	Ω
Q_g	Total Gate Charge	$I_D=3A$	---	20	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=960V$	---	7.5	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$	---	5.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=600V$, $I_D=3A$ $R_G=10\Omega$	---	15	---	ns
T_r	Rise Time		---	20	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	76	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	850	---	pF
C_{oss}	Output Capacitance		---	55	---	
C_{rss}	Reverse Transfer Capacitance		---	0.8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	3	A
I_{SM}	Pulsed Source Current		---	---	12	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=3A$, $T_J=25^{\circ}\text{C}$	---	0.83	1.5	V

Notes:

1.The EAS data shows Max. rating .The test condition is $V_{DS}=100V$, $V_{GS}=10V$, $L=20mH$, $I_{AS}=2.5A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

